

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	32	("6483156" "20020167007" "6716684" "6475869" "20020081794" "6376317" "5716879" "5563077" "6680240" "5578513" "5658806" "6562665" "6525403" "5346839" "6413802" "6730964" "6611029"). PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/16 10:12
S2	0	S1 and metal adj film and opposite adj sidewalls	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:14
S3	1	S1 and metal adj film	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:34
S4	83	opposite adj sidewall and gate adj electrode and gate adj dielectric	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:39
S5	23	opposite adj sidewall and gate adj electrode and gate adj dielectric and SOI	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:22
S6	92	("4589928" "5923066" "6090713" "4261761" "4863562" "5455547" "5537083" "5589082" "6218208" "6218208" "4249190" "6147381" "5952701" "4466175" "4899202" "4906587" "4946799" "4965213" "5293058" "5808346" "5930630" "6194289" "4270137" "4786609" "5397720" "5508555" "5541436" "5821575" "5877978" "5918114" "5930605" "6040212" "6060364" "6081443" "6124613" "6225662" "6225662" "6228698" "6238960" "4378628" "4460911" "4476545" "4599576" "4823180" "4929991" "4969022" "5442584" "5504027" "5663578" "5696396").pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:44
S7	1	opposite adj sidewall near5 semiconductor adj body and gate adj electrode and gate adj dielectric and SOI	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:23

S8	13	("20020081794" "20020167007" "5563077" "5578513" "5658806" "5716879" "6376317" "6413802" "6475869" "6483156" "6611029" "6680240" "6716684").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/16 12:53
S9	6180	gate electrode and work function and metal film	US-PGPUB; USPAT; USOCR	AND	OFF	2005/03/16 12:53
S11	3561	gate electrode and work function same metal film	US-PGPUB; USPAT; USOCR	AND	ON	2005/03/16 12:55
S12	1901	gate electrode same work function same metal film	US-PGPUB; USPAT; USOCR	AND	ON	2005/03/16 12:56
S13	847	gate electrode same work function same metal film and p-type	US-PGPUB; USPAT; USOCR	AND	ON	2005/03/16 12:56
S14	49	gate electrode same work function same metal film	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/03/16 12:59
S15	350	work function same metal film	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/03/16 12:59
S16	149	work function same metal film and gate electrode	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/03/16 12:59
S17	4	"6858478".pn. "20040142567".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 11:01
S18	34	("20020081794" "20020167007" "5346839" "5563077" "5578513" "5658806" "5716879" "6376317" "6413802" "6475869" "6483156" "6525403" "6562665" "6611029" "6680240" "6716684" "6730964").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 12:58
S19	296	"18" and workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 12:58

S20	34	("20020081794" "20020167007" "5346839" "5563077" "5578513" "5658806" "5716879" "6376317" "6413802" "6475869" "6483156" "6525403" "6562665" "6611029" "6680240" "6716684" "6730964"). PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 12:58
S21	1	S20 and workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 13:14
S22	99	gate adj electrode same workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 14:53
S23	260	gate same workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 14:58
S24	319	semiconductor and workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 16:20
S25	304	MOS\$3 and workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 14:57
S26	348	S24 or S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 14:57
S27	275	S24 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 14:57
S28	11	gate same workfunction and "4.0"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 15:00
S29	11	gate and workfunction and "4.0"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 15:04

S30	279	gate and workfunction and "4"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 15:05
S31	38	gate and workfunction same "4"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 15:05
S32	1	semiconductor and workfunction same "4\$3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 16:17
S33	9	finfet and metal adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/08 12:03
S34	403	finfet and metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/08 12:03
S35	253	finfet and metal near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/08 12:30
S36	190	finfet and metal near5 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/08 17:23
S37	35	finfet and metal near5 gate adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/08 17:23